ESD Protection Diodes, Low Capacitance, Dual Channel

The ESD7272 is designed to protect various IOs and data lines from ESD. The low capacitance and low ESD clamping voltage combined with a high standoff voltage makes this device an ideal solution for protecting various types of ICs without causing signal degradation. The small, cost efficient SOT-23 package allows for easy PCB layout and BOM reduction on multiple pin modules.

Features

- Low Capacitance: < 3.0 pF
- Protection for the Following IEC & ISO Standards:
 - ◆ IEC 61000-4-2 (Level 4)
 - ISO 10605
- Low ESD Clamping Voltage
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Sensor Lines
- PWM Inputs/Outputs
- General I/Os
- Automotive

MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

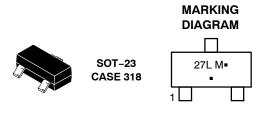
Rating	Symbol	Value	Unit
IEC 61000–4–2 Contact IEC 61000–4–2 Air ISO 10605 330 pF / 330 Ω Contact ISO 10605 330 pF / 2 kΩ Contact ISO 10605 150 pF / 2 kΩ Contact	ESD	±15 ±15 ±12 ±25 ±30	kV
Operating Junction Temperature Range	T _{J(max)}	–55 to +175	°C
Storage Temperature Range	T _{stg}	–55 to +175	°C
Lead Solder Temperature – Maximum (10 Second Duration)	ΤL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com



⁼ Specific Device Code

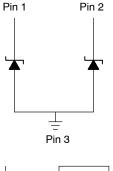
= Date Code

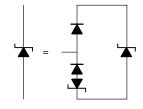
27L

Μ

= Pb-Free Package

PIN CONFIGURATIONS AND SCHEMATICS





ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

ESD7272

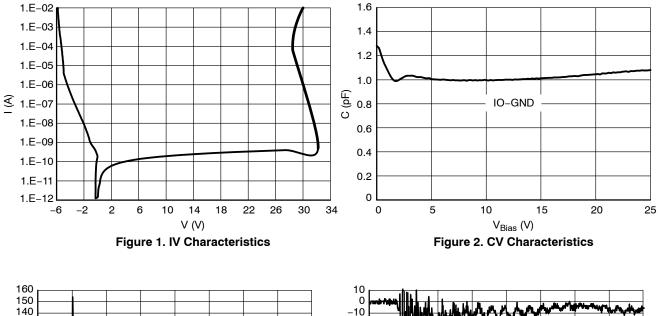
Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Reverse Working Voltage	V _{RWM}	Any I/O to GND			24	V
Breakdown Voltage	V _{BR}	I _T = 1 mA, Any I/O to GND	27	29	36	V
Forward Voltage	V _F	I _T = 100 mA, GND to Any I/O	2.0	6.0		V
Reverse Leakage Current	I _R	V _{RWM} = 24 V, Any I/O to GND		0.2	1000	nA
Clamping Voltage	V _C	I _{PP} = 1 A, Any I/O to GND (8/20 μs pulse)		38	40	V
Clamping Voltage (Note 1)	V _C	IEC61000-4-2, ±8kV Contact	See	See Figures 3 & 4		
Clamping Voltage TLP (Note 2)	V _C	Ipp = 8 A Ipp = 16 A Ipp = -8 A Ipp = -16 A		38 41 -8.0 -10.5		V V V V
Junction Capacitance	CJ	V _R = 0 V, f = 1 MHz between Any I/O and GND		1.3	2.0	pF

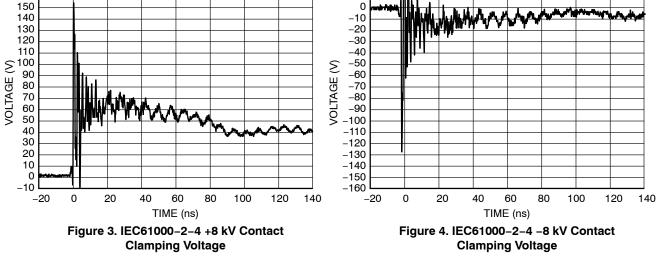
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. For text procedures see Application Note AND8307/D.

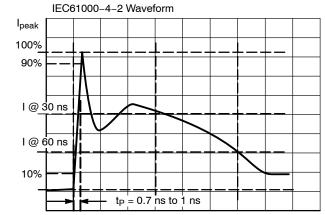
2. ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50 \Omega$, $t_p = 100$ ns, $t_r = 4$ ns, averaging window; $t_1 = 30$ ns to $t_2 = 60$ ns.





IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)	
1	2	7.5	4	2	
2	4	15	8	4	
3	6	22.5	12	6	
4	8	30	16	8	





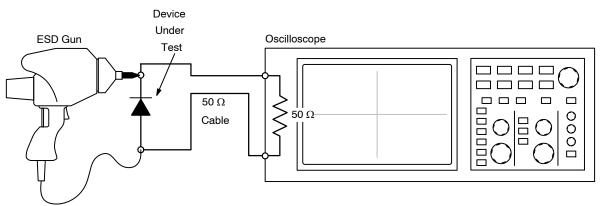


Figure 6. Diagram of ESD Clamping Voltage Test Setup

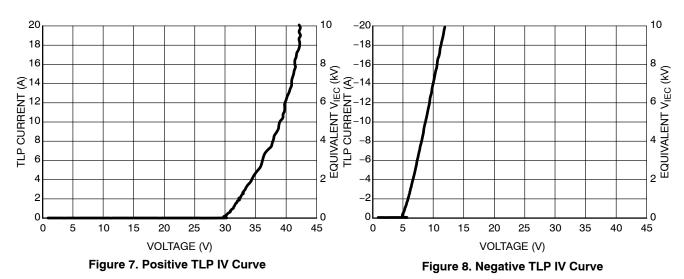
The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000–4–2 waveform. Since the IEC61000–4–2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

ESD7272



NOTE: TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100$ ns, $t_r = 300$ ps, averaging window: $t_1 = 30$ ns to $t_2 = 60$ ns.

Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I–V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 9. TLP I–V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 10 where an 8 kV IEC 61000–4–2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I–V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

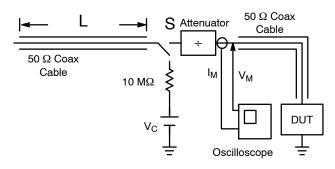


Figure 9. Simplified Schematic of a Typical TLP System

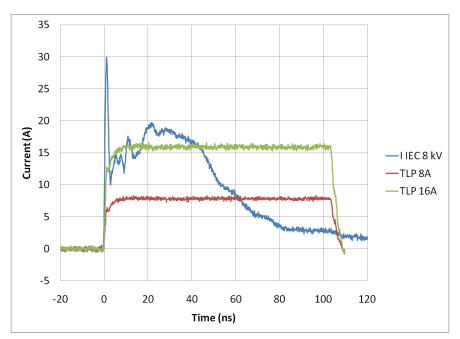


Figure 10. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
ESD7272LT1G	SOT-23	SOT-23	3000 / Tape & Reel
SZESD7272LT1G*	27L	(Pb-Free)	SUUU/ Tape & neer

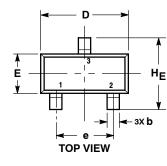
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S2 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

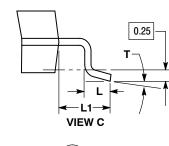
Capable.

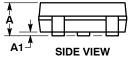
ESD7272

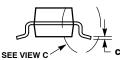
PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AS**









END VIEW

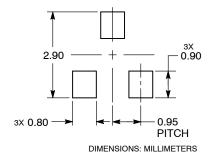
NOTES: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF

- 2. 3
- THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- 4 PROTRUSIONS, OR GATE BURRS

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.039	0.044	
A1	0.01	0.06	0.10	0.000	0.002	0.004	
σ	0.37	0.44	0.50	0.015	0.017	0.020	
c	0.08	0.14	0.20	0.003	0.006	0.008	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Е	1.20	1.30	1.40	0.047	0.051	0.055	
e	1.78	1.90	2.04	0.070	0.075	0.080	
Г	0.30	0.43	0.55	0.012	0.017	0.022	
L1	0.35	0.54	0.69	0.014	0.021	0.027	
HE	2.10	2.40	2.64	0.083	0.094	0.104	
Т	0°		10°	0°		10°	







ON Semiconductor and ware trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability, arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

Phone: 421 33 790 2910

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative